Abstracts

Very High Isolation Optoelectronic Switch Using PIN-PD and GaAs MESFET Transmission Gate

Q.Z. Liu and R.I. MacDonald. "Very High Isolation Optoelectronic Switch Using PIN-PD and GaAs MESFET Transmission Gate." 1994 MTT-S International Microwave Symposium Digest 94.3 (1994 Vol. III [MWSYM]): 1387-1390.

A novel broadband optoelectronic switch is demonstrated experimentally with very high isolation. The switch consists of a switching PIN photodiode followed by a GaAs MESFET in common gate configuration as a transmission gate. Isolation level higher than 70.0 dB at DC and 55.0 dB at 1.0 GHz was obtained, respectively.

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